

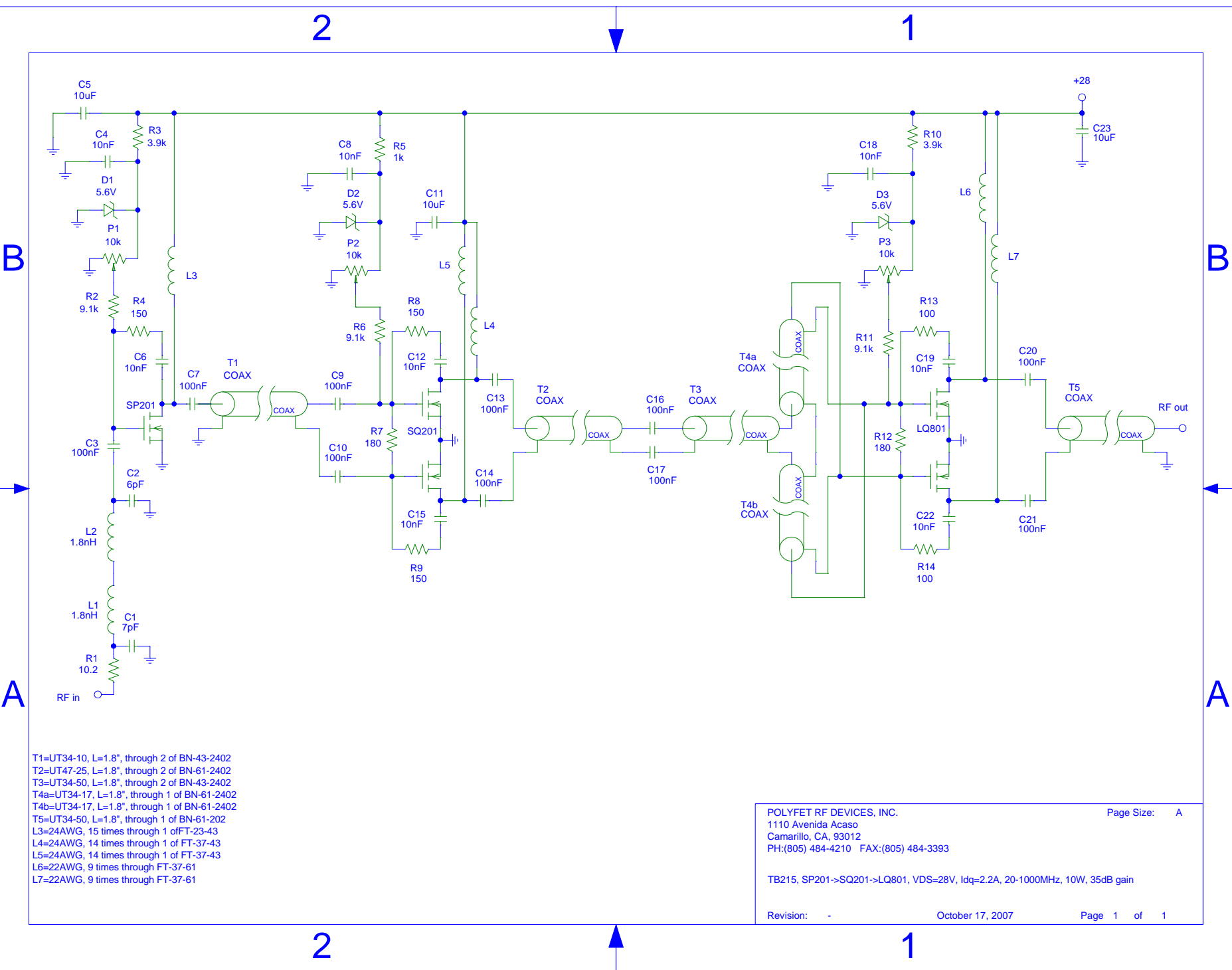
SYMBOL	VALUE	DESCRIPTION
C1	7pF	0805 chip cap
C2	6pF	0805 chip cap
C3	100nF	0805 chip cap
C4, C8, C18	10nF	0805 chip cap
C5, C11, C23	10uF	50V tantalum
C6,12,15,19,22	10nF	ATC-200B Chip Cap
C7,9,10,13,14,16,17,20,21	100nF	ATC-200B Chip Cap
R1	10.2	0805 chip resistor
R2, R6, R11	9.1k	0805 chip resistor
R3, R5, R10	3.9k	0805 chip resistor
R4, R8, R9	150	1 Watt Axial
R7, R12	180	0805 chip resistor
R13, R14	100	20W Flanged R
D1, D2, D3	5.6V	Zener Diode
P1, P2, P3	10k	6mm multi-turn pot
L1, L2	1.8nH	0805 chip inductor
L3	24AWG	15x, 1 of FT-23-43
L4, L5	24AWG	14x, 1 of FT-37-43
L6, L7	22AWG	9 times through FT-37-61
Q1	SP201	Polyfet Transistor
Q2	SQ201	Polyfet Transistor
Q3	LQ801	Polyfet Transistor
T1	1.8"	UT34-10, 1 of FB-43-101
T2	1.8"	UT47-25, 2 of BN-61-2402
T3	1.8"	UT34-50, 1 of FB-43-101
T4	1.8"	UT34-17, 1 of BN-61-2402
T5	1.8"	UT34-25, 1 of BN-61-202
Vdd	28V	Drain Voltage
Bias	0.8A	0.2A+0.4A+1.6A

PCB= Teflon, er=2.55, 1oz, thickness = 30mil

DRN BY: Cunningham	10/15/07
CHKD :	
ELECT : Cunningham	10/15/07
MECH : Cunningham	10/15/07
PRDC :	
QUAL :	
PGMS :	

## POLYFET RF DEVICES

TB215 SP201->SQ201->LQ801 20-1000MHz 10W 35dB			
SIZE	FSCM NO	Vdd=28V Idq=2.2A	REV A
SCALE : 1	: 1	SHEET 1	OF 1



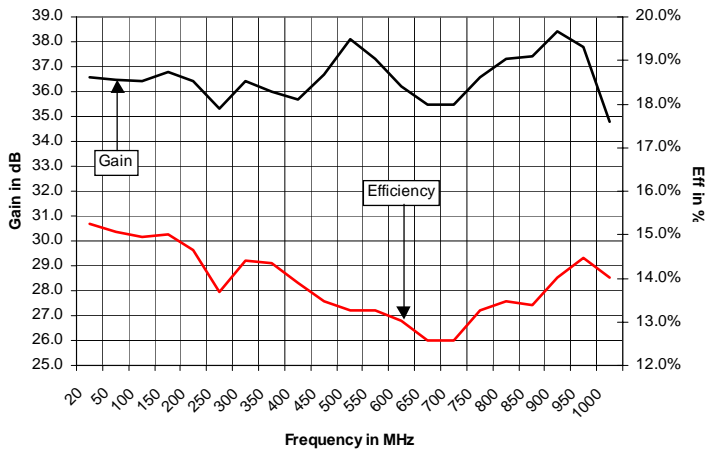
T1=UT34-10, L=1.8", through 2 of BN-43-2402  
 T2=UT47-25, L=1.8", through 2 of BN-61-2402  
 T3=UT34-50, L=1.8", through 2 of BN-43-2402  
 T4a=UT34-17, L=1.8", through 1 of BN-61-2402  
 T4b=UT34-17, L=1.8", through 1 of BN-61-2402  
 T5=UT34-50, L=1.8", through 1 of BN-61-202  
 L3=24AWG, 15 times through 1 of FT-23-43  
 L4=24AWG, 14 times through 1 of FT-37-43  
 L5=24AWG, 14 times through 1 of FT-37-43  
 L6=22AWG, 9 times through FT-37-61  
 L7=22AWG, 9 times through FT-37-61

POLYFET RF DEVICES, INC.  
 1110 Avenida Acaso  
 Camarillo, CA, 93012  
 PH:(805) 484-4210 FAX:(805) 484-3393

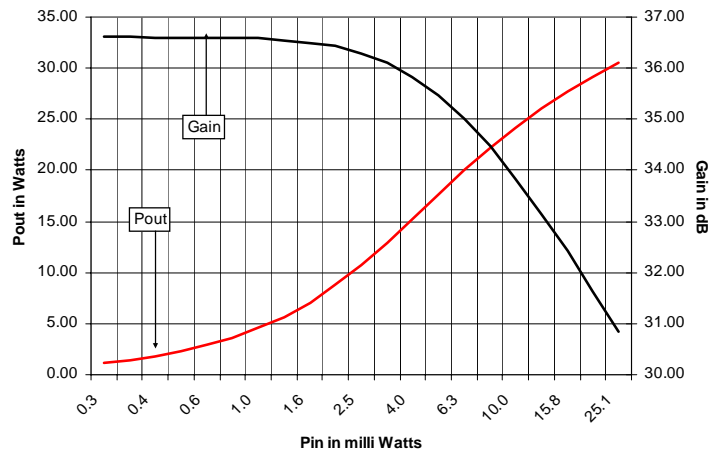
TB215, SP201->SQ201->LQ801, VDS=28V, Idq=2.2A, 20-1000MHz, 10W, 35dB gain

Revision: - October 17, 2007 Page 1 of 1

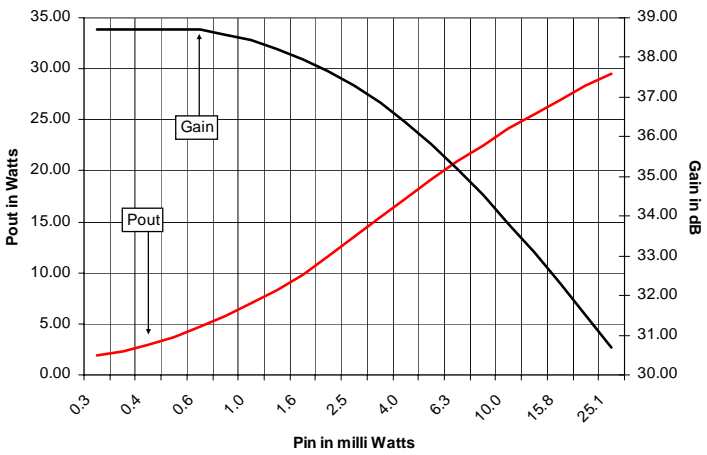
TB215 Gain/Eff vs Freq, Vds=28V, Idq=2.2A Pout=10W



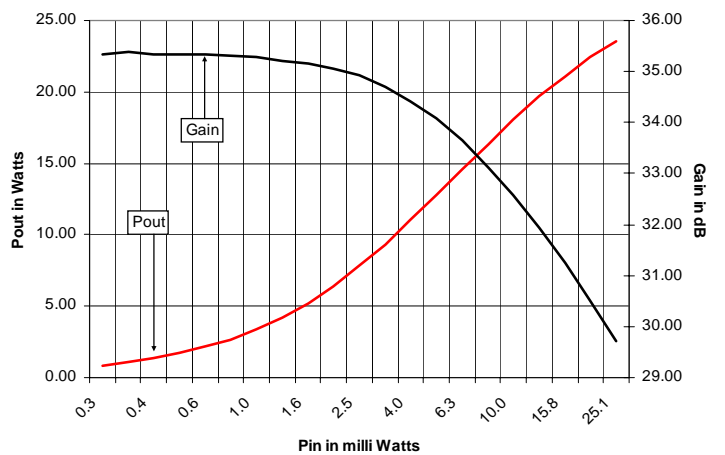
TB215 Pout/Gain vs Pin, Freq=20MHz, Vds=28V, Idq=2.2A



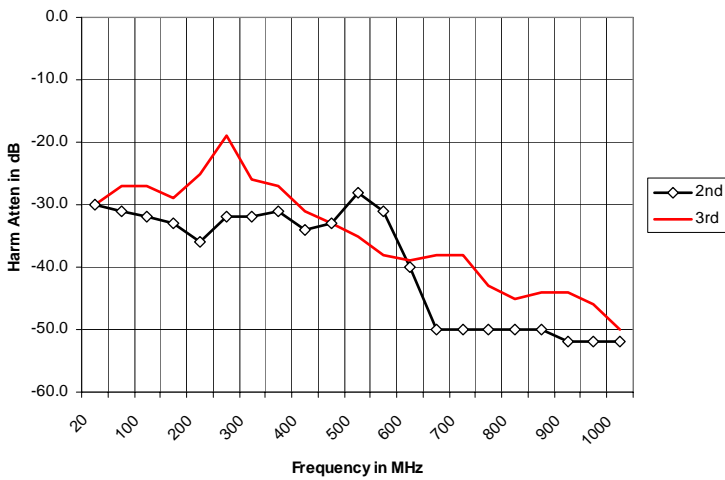
TB215 Pout/Gain vs Pin, Freq=500MHz, Vds=28V, Idq=2.2A



TB215 Pout/Gain vs Pin, Freq=1000MHz, Vds=28V, Idq=2.2A



TB215 Harm vs Freq, Vds=28V, Idq=2.2A, Pout=10W



TB215 IM vs Freq, Vds=28V, Idq=2.2A, PEP=10W

